

BAP70-02

Silicon PIN diode

Rev. 05 — 2 January 2008

Product data sheet

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NXP Semiconductors

Silicon PIN diode

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FEATURES

- High voltage, current controlled RF resistor for attenuators
- Low diode capacitance
- Very low series inductance.

APPLICATIONS

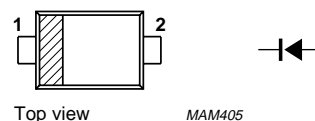
- RF attenuators
- (SAT)TV
- Car radio.

DESCRIPTION

Planar PIN diode in a SOD523 ultra small SMD plastic package.

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | cathode |
| 2 | anode |



Marking code: K8.

Fig.1 Simplified outline (SOD523) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-----------|----------------------------|----------------------|------|------|------|
| V_R | continuous reverse voltage | | – | 50 | V |
| I_F | continuous forward current | | – | 100 | mA |
| P_{tot} | total power dissipation | $T_s = 90\text{ °C}$ | – | 415 | mW |
| T_{stg} | storage temperature | | –65 | +150 | °C |
| T_j | junction temperature | | –65 | +150 | °C |

ELECTRICAL CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | TYP. | MAX. | UNIT |
|----------|--------------------------|--|------|------|---------------|
| V_F | forward voltage | $I_F = 50\text{ mA}$ | 0.9 | 1.1 | V |
| I_R | reverse leakage current | $V_R = 50\text{ V}$ | – | 100 | nA |
| C_d | diode capacitance | $V_R = 0\text{ V}; f = 1\text{ MHz}$ | 570 | – | fF |
| | | $V_R = 1\text{ V}; f = 1\text{ MHz}$ | 400 | – | fF |
| | | $V_R = 5\text{ V}; f = 1\text{ MHz}$ | 270 | – | fF |
| | | $V_R = 20\text{ V}; f = 1\text{ MHz}$ | 200 | 250 | fF |
| r_D | diode forward resistance | $I_F = 0.5\text{ mA}; f = 100\text{ MHz}$ | 77 | 100 | Ω |
| | | $I_F = 1\text{ mA}; f = 100\text{ MHz}$ | 40 | 50 | Ω |
| | | $I_F = 10\text{ mA}; f = 100\text{ MHz}$ | 5.4 | 7 | Ω |
| | | $I_F = 100\text{ mA}; f = 100\text{ MHz}$ | 1.4 | 1.9 | Ω |
| τ_L | charge carrier life time | when switched from $I_F = 10\text{ mA}$ to $I_R = 6\text{ mA}$; $R_L = 100\text{ }\Omega$; measured at $I_R = 3\text{ mA}$ | 1.25 | – | μs |
| L_S | series inductance | $I_F = 100\text{ mA}; f = 100\text{ MHz}$ | 0.6 | – | nH |

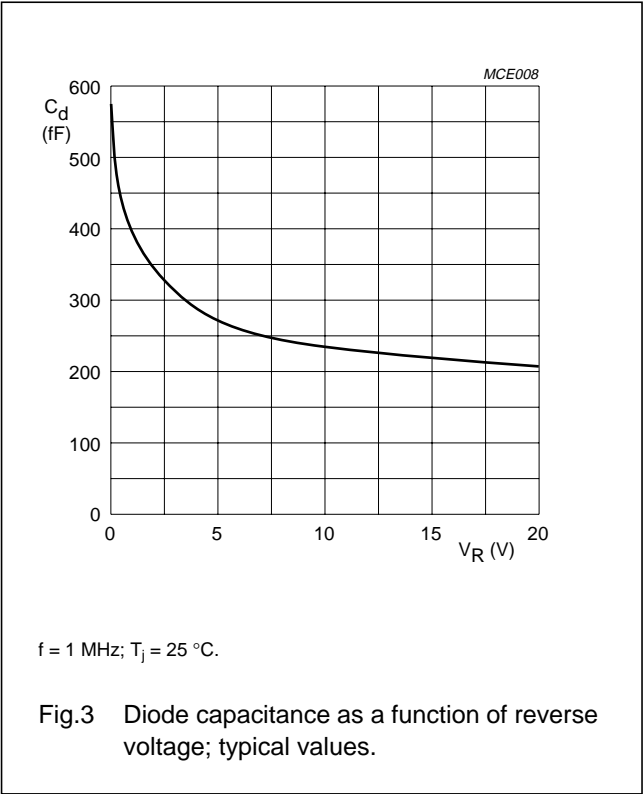
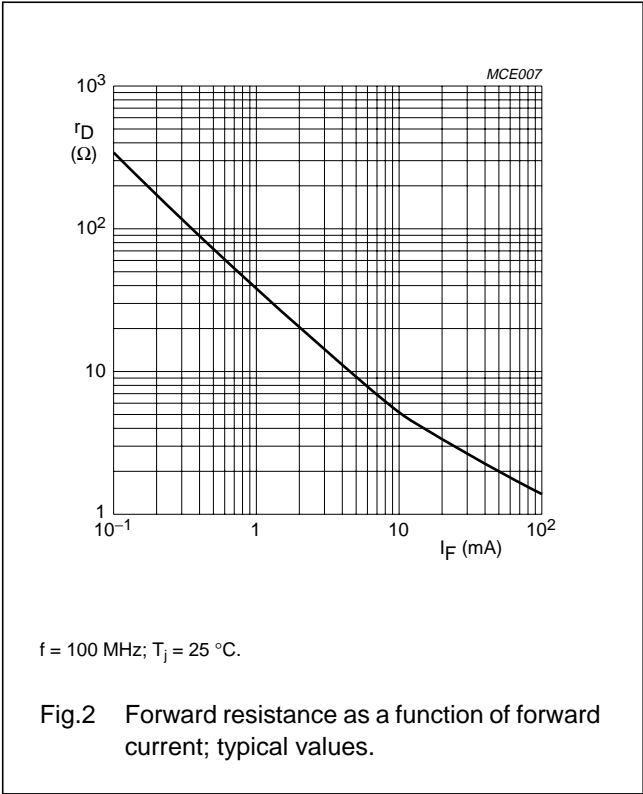
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THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | VALUE | UNIT |
|---------------|---|-------|------|
| $R_{th\ j-s}$ | thermal resistance from junction to soldering point | 145 | K/W |

GRAPHICAL DATA



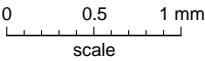
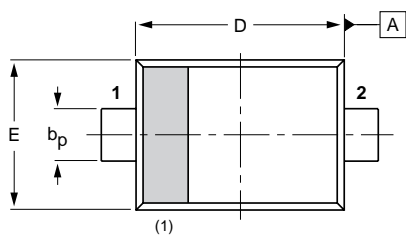
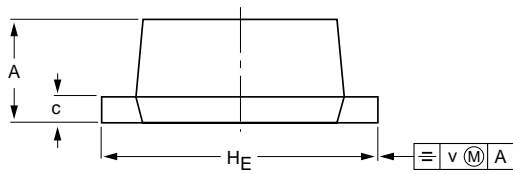
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PACKAGE OUTLINE

Plastic surface-mounted package; 2 leads

SOD523



DIMENSIONS (mm are the original dimensions)

| UNIT | A | b _p | c | D | E | H _E | v |
|------|--------------|----------------|--------------|--------------|--------------|----------------|-----|
| mm | 0.65 0.58 | 0.34 0.26 | 0.17 0.11 | 1.25 1.15 | 0.85 0.75 | 1.65 1.55 | 0.1 |

Note
1. The marking bar indicates the cathode.

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|--------------------|------------|-------|-------|--|------------------------|----------------------|
| | IEC | JEDEC | JEITA | | | |
| SOD523 | | | SC-79 | | | 02-12-13 06-03-16 |

Legal information

Data sheet status

| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Revision history

Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|--|--------------|---------------------------|---------------|--------------|
| BAP70-02_N_5 | 20080102 | Product data sheet | - | BAP70-02_N_4 |
| Modifications: <ul style="list-style-type: none">Package outline drawing on page 4 changed | | | | |
| BAP70-02_N_4 | 20070322 | Product data sheet | - | BAP70-02_3 |
| BAP70-02_3 (9397 750 10093) | 20020806 | Product specification | - | BAP70-02_N_2 |
| BAP70-02_N_2 (9397 750 10079) | 20020702 | Preliminary specification | - | BAP70-02_N_1 |
| BAP70-02_N_1 (9397 750 09578) | 20020402 | Preliminary specification | - | - |

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